

	Type	Hits	Search Text	DBs
33	BRS	101	257/197.ccls. and ((back or backside) with (gate or electrode or conductor or contact))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
35	BRS	63	257/565.ccls. and ((back or backside) with (electrode or gate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
37	BRS	207	(257/526).ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
40	BRS	38	(257/587 or 257/592).ccls. and (back near2 gate or backgate or back adj side or backside)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
41	BRS	142	(257/E29.171,E29.183,E29.189,E29.19,E29.198).ccls. and ((back near4 (electrode or gate or conductor)) or backgate)	US-PGPUB; USPAT; EPO; JPO; DERWENT
42	BRS	147	(257/E29.171,E29.183,E29.189,E29.19,E29.198).ccls. and ((back near4 (electrode or gate or conductor)) or backgate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
43	BRS	195	semiconductor and (((back or buried) with (gate or electrode)) or backgate) and (inversion or accumul\$5) and (vertical\$4 near5 bipolar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
44	BRS	203	semiconductor and (((back or buried) with (gate or electrode)) or backgate) and (inversion or accumul\$5) and (vertical\$4 near5 bipolar)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB